

**Notice of References Cited**

Application/Control No.

09/928,356

Applicant(s)/Patent Under Reexam

Lempkowski et al.

Examiner

B. William Baumeister

Art Unit

2815

Page 1 of 2

**U.S. PATENT DOCUMENTS**

	Document Number Country Code-Number-Kind Code	Date MM-YYYY <sup>1</sup>	Name	Classification <sup>2</sup>
A				
B				
C				
D				
E				
F				
G				
H				
I				
J				
K				
L				
M				

**FOREIGN PATENT DOCUMENTS**

	Document Number Country Code-Number-Kind Code	Date MM-YYYY <sup>1</sup>	Country	Name	Classification <sup>2</sup>
N					
O					
P					
Q					
R					
S					
T					

**NON-PATENT DOCUMENTS**

	Include, as applicable: Author, Title, Date, Publisher, Edition or Volume, Pertinent Pages
U	Eisenbeiser et al., Field effect transistors with SrTiOs gate dielectric on Si," 6 March 2000, Applied Physics Letters, Vol. 76, No. 10, pp.1324-1326.
V	Weiss, "Speed demon gets hooked on silicon," Science News Online, 9/15/2001.
W	"Motorola develops new super-fast chip," USA Today, 9/4/2001.
X	Valigra, "Motorola Lays GaAs on Si Wafer," AsiaBiz Tech, Nov. 2001.

\* A copy of this reference is not being furnished with this Office action. See MPEP § 707.05(a).

<sup>1</sup> Dates in MM-YYYY format are publication dates.<sup>2</sup> Classifications may be U.S. or foreign.

<b>Notice of References Cited</b>	Application/Control No. <b>09/928,356</b>	Applicant(s)/Patent Under Reexam <b>Lempkowski et al.</b>	
	Examiner <b>B. William Baumeister</b>	Art Unit <b>2815</b>	Page 2 of 2

**U.S. PATENT DOCUMENTS**

	Document Number Country Code-Number-Kind Code	Date MM-YYYY <sup>1</sup>	Name	Classification <sup>2</sup>
A				
B				
C				
D				
E				
F				
G				
H				
I				
J				
K				
L				
M				

**FOREIGN PATENT DOCUMENTS**

	Document Number Country Code-Number-Kind Code	Date MM-YYYY <sup>1</sup>	Country	Name	Classification <sup>2</sup>
N					
O					
P					
Q					
R					
S					
T					

**NON-PATENT DOCUMENTS**

	Include, as applicable: Author, Title, Date, Publisher, Edition or Volume, Pertinent Pages
U	"Holy Grail! Motorola claims high-yield GaAs breakthrough," Micromagazine.com (no date available).
V	
W	
X	

<sup>1</sup> A copy of this reference is not being furnished with this Office action. See MPEP § 707.05(e).

<sup>1</sup> Dates in MM-YYYY format are publication dates.

<sup>2</sup> Classifications may be U.S. or foreign.